

isc N-Channel MOSFET Transistor

2SK1411

DESCRIPTION

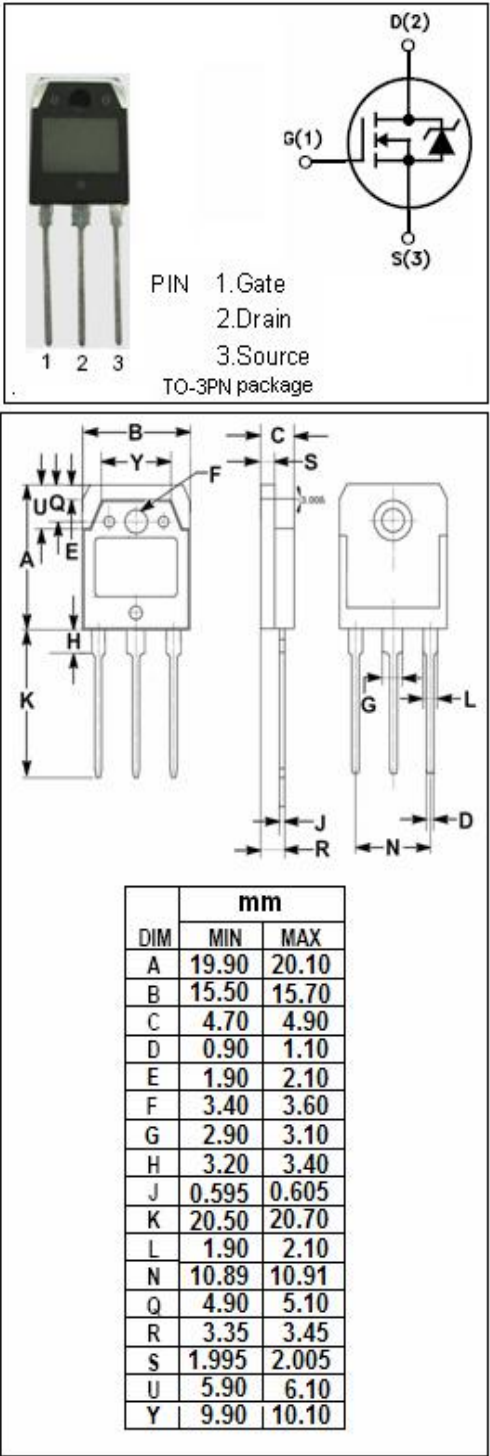
- Drain Current $-I_D=20A$ @ $T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}=500$ (Min)

APPLICATIONS

- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNI T
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^{\circ}C$	20	A
P_{tot}	Total Dissipation@ $TC=25^{\circ}C$	250	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc N-Channel Mosfet Transistor**2SK1411****• ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=10\text{mA}$	500			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=0\text{V}$; $I_D=1\text{mA}$	2.0	3.0	4.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}$; $I_D=10\text{A}$			0.30	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=\pm 20\text{V}$; $V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=500\text{V}$; $V_{GS}=0$			500	μA